

OPA7735H

Infrared LED Chip

High Speed

GaAlAs /GaAs

1. Material Substrate GaAs (N Type)
Epitaxial Layer GaAlAs (N/P Type)

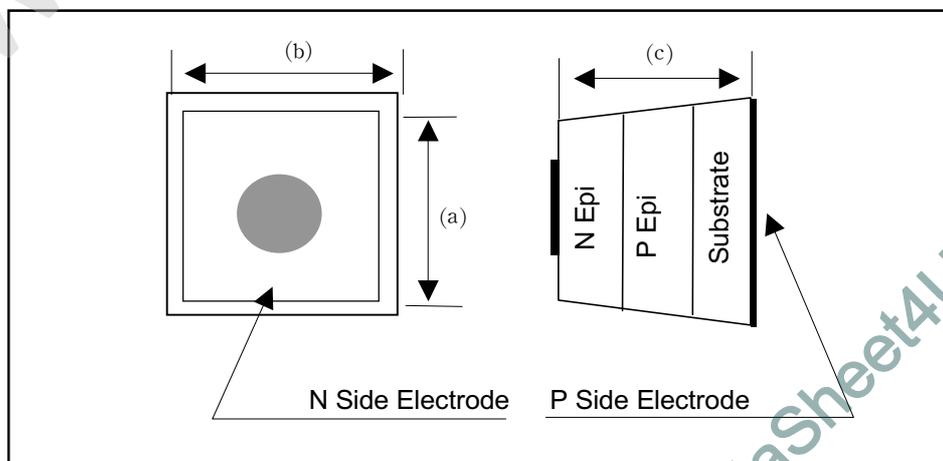
2. Electrode N (Cathode) Side Gold Alloy
P (Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.7	2.0	V	$I_F=20\text{mA}$
	$V_{F(2)}$		2.0	2.5	V	$I_F=100\text{mA}$
Reverse Voltage	V_R	5.0			V	$I_R=10\mu\text{A}$
Power	$P_{O(1)}$		1		mW	$I_F=20\text{mA}$
	$P_{O(2)}$		4		mW	$I_F=100\text{mA}$
Wavelength	λ_P		770		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		30		nm	$I_F=20\text{mA}$
Rise Time	t_r		40		ns	$I_F=50\text{mA}$

Note : Assembled into TO-18 Header without resin coating.

4. Mechanical Data (a) Emission Area ----- 12mil \times 12mil
(b) Bottom Area ----- 14mil \times 14mil
(c) Chip Thickness ----- 10mil



Knowledge*on Inc.

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